

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
26 May 2005 (26.05.2005)

PCT

(10) International Publication Number
WO 2005/048354 A1

(51) International Patent Classification⁷: **H01L 29/786**

(21) International Application Number:
PCT/JP2004/016797

(22) International Filing Date:
5 November 2004 (05.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-386021 14 November 2003 (14.11.2003) JP

(71) Applicant (for all designated States except US): SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 243-0036 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): KANNO, Yohei
[JP/JP]; c/o Semiconductor Energy Laboratory Co., Ltd.,
398, Hase, Atsugi-shi, Kanagawa 243-0036 (JP). FUJII,
Gen [JP/JP]; c/o Semiconductor Energy Laboratory Co.,
Ltd., 398, Hase, Atsugi-shi, Kanagawa 243-0036 (JP).

(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

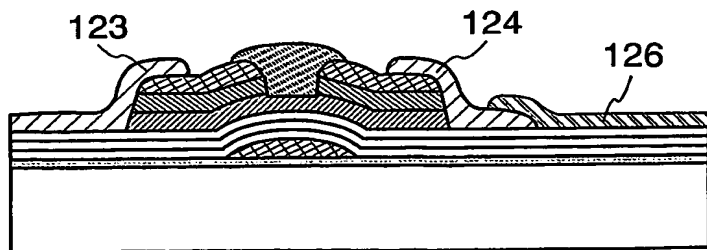
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,
SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR ELEMENT, METHOD FOR MANUFACTURING THE SAME, LIQUID CRYSTAL DISPLAY
DEVICE, AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: In case that a conventional
TFT is formed to have an inversely
staggered type, a resist mask is required
to be formed by an exposing, developing,
and droplet discharging in forming an
island-like semiconductor region. It
resulted in the increase in the number of
processes and the number of materials.
According to the present invention, a
process can be simplified since after
forming a source region and a drain
region, a portion serving as a channel

region is covered by an insulating film serving as a channel protecting film to form an island-like semiconductor film, and so a
semiconductor element can be manufactured by using only metal mask without using a resist mask.